

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>A</sub> = +25°C
60V	3Ω @ V <sub>GS</sub> = 10V	310mA
	4Ω @ V <sub>GS</sub> = 5V	270mA

## Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

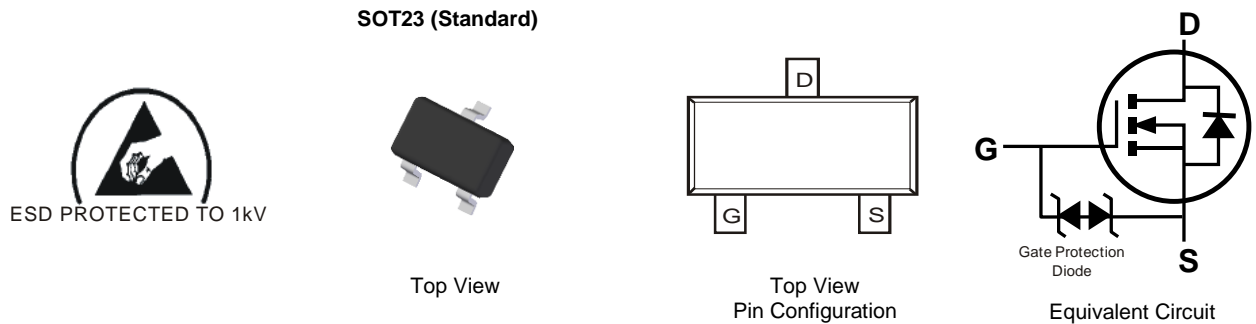
- DC-DC converters
- Power-management functions
- Battery operated systems and solid-state relays
- Drivers: relays, solenoids, lamps, hammers, displays, memories, transistors, etc.

## Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface-Mount Package
- ESD Protected Gate
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **An automotive-compliant part is available under separate datasheet ([DMN65D8LQ](#))**

## Mechanical Data

- Package: SOT23
- Package Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Solderable per MIL-STD-202, Method 208. Lead Free Plating. Matte Tin Finish Annealed over Alloy 42 Leadframe <sup>Ⓔ3</sup>
- Terminal Connections: See Diagram
- Weight: 0.008487 grams (Approximate)

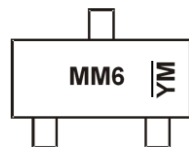


## Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMN65D8L-7	SOT23 (Standard)	3,000	Tape & Reel
DMN65D8L-13	SOT23 (Standard)	10,000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



MM6 = Product Type Marking Code  
 YM or YM = Date Code Marking  
 Y or Y = Year (ex: K = 2023)  
 M or M = Month (ex: 9 = September)

### Date Code Key

Year	2012	...	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032
Code	Z	...	K	L	M	N	P	R	S	T	U	V

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	310	mA
		T <sub>A</sub> = +70°C		240	
Continuous Drain Current (Note 6) V <sub>GS</sub> = 5V	Steady State	T <sub>A</sub> = +25°C	I <sub>D</sub>	270	mA
		T <sub>A</sub> = +70°C		210	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	800	mA
Maximum Body Diode Continuous Current (Note 6)			I <sub>S</sub>	310	mA

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation	(Note 6)	P <sub>D</sub>	370	mW
	(Note 5)		540	
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>θJA</sub>	348	°C/W
	(Note 5)		241	
Thermal Resistance, Junction to Case	(Note 5)	R <sub>θJC</sub>	91	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1.0	µA	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V
Gate-Body Leakage	I <sub>GSS</sub>	—	—	±5	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.2	—	2.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	1.9	3	Ω	V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.115A
		—	2.2	4	Ω	V <sub>GS</sub> = 5V, I <sub>D</sub> = 0.115A
Forward Transconductance	g <sub>FS</sub>	80	290	—	ms	V <sub>DS</sub> = 10V, I <sub>D</sub> = 0.115A
Diode Forward Voltage	V <sub>SD</sub>	—	0.8	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>ISS</sub>	—	22	—	pF	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz
Output Capacitance	C <sub>OSS</sub>	—	3.2	—		
Reverse Transfer Capacitance	C <sub>RSS</sub>	—	2.0	—		
Gate Resistance	R <sub>g</sub>	—	79.9	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	—	0.87	—	nC	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 30V, I <sub>D</sub> = 150mA
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	—	0.43	—		
Gate-Source Charge	Q <sub>gs</sub>	—	0.11	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	0.11	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	2.7	—	ns	V <sub>DD</sub> = 30V, I <sub>D</sub> = 0.115A, V <sub>GEN</sub> = 10V, R <sub>GEN</sub> = 25Ω
Turn-On Rise Time	t <sub>r</sub>	—	2.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	12.6	—		
Turn-Off Fall Time	t <sub>f</sub>	—	7.3	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
  - Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

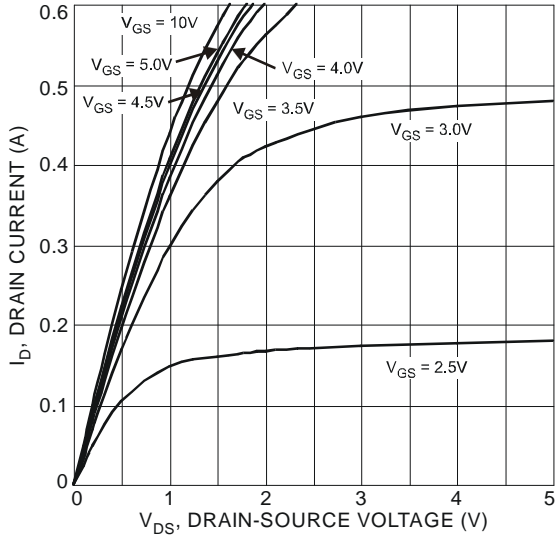


Figure 1. Typical Output Characteristic

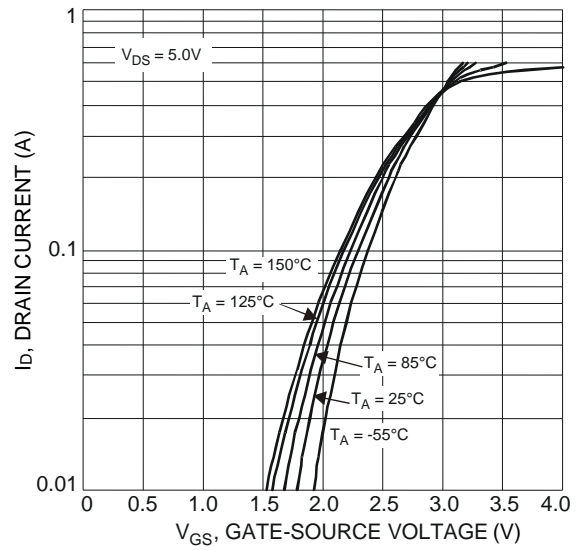


Figure 2. Typical Transfer Characteristics

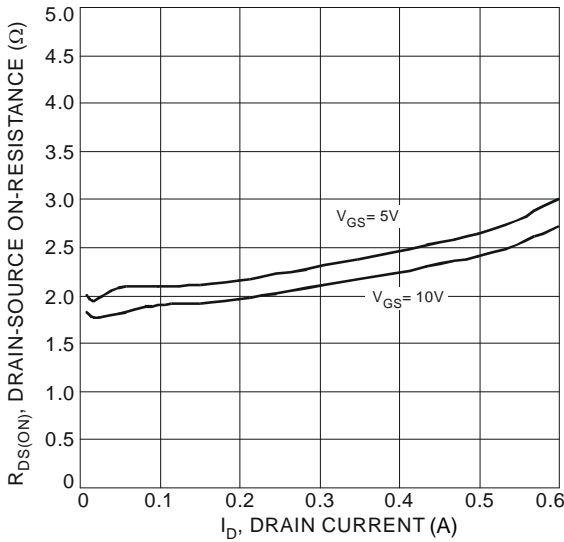


Figure 3. Typical On-Resistance vs. Drain Current and Temperature

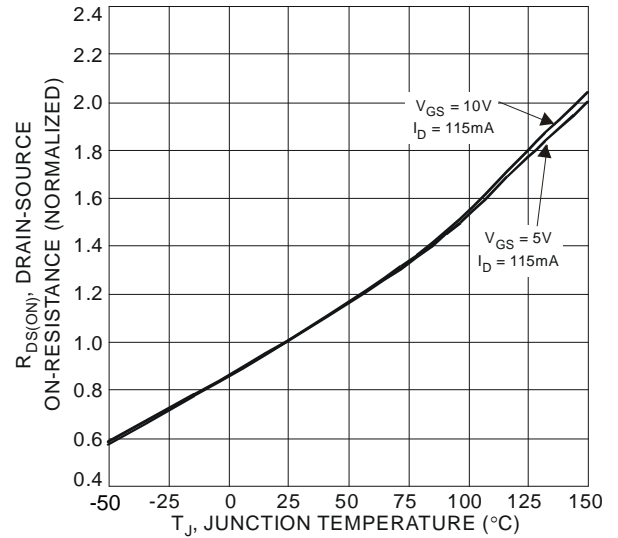


Figure 4. On-Resistance Variation with Temperature

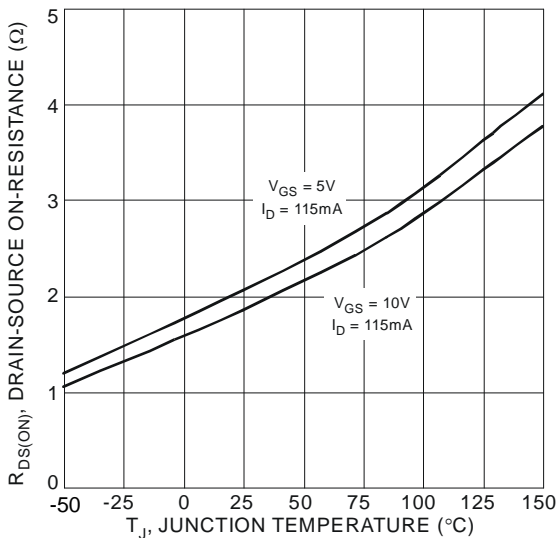


Figure 5. On-Resistance Variation with Temperature

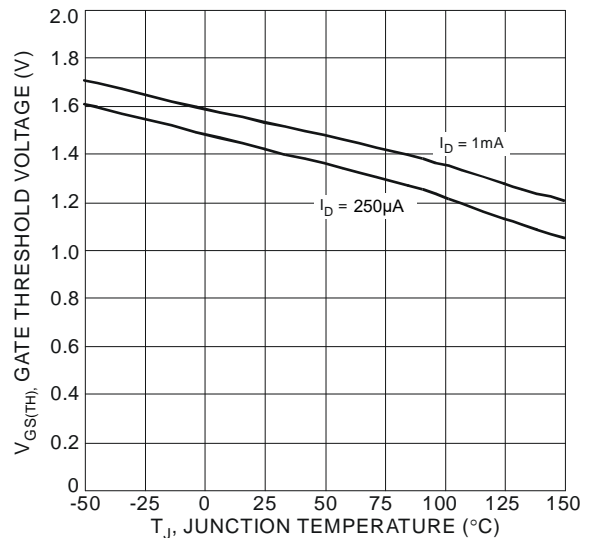


Figure 6. Gate Threshold Variation vs. Junction Temperature

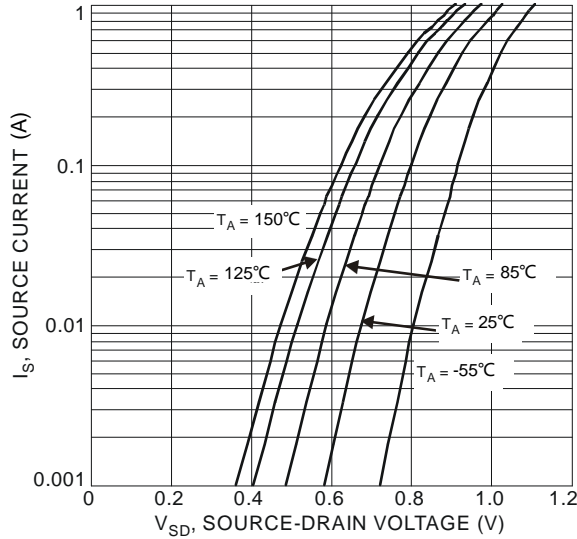


Figure 7. Diode Forward Voltage vs. Current

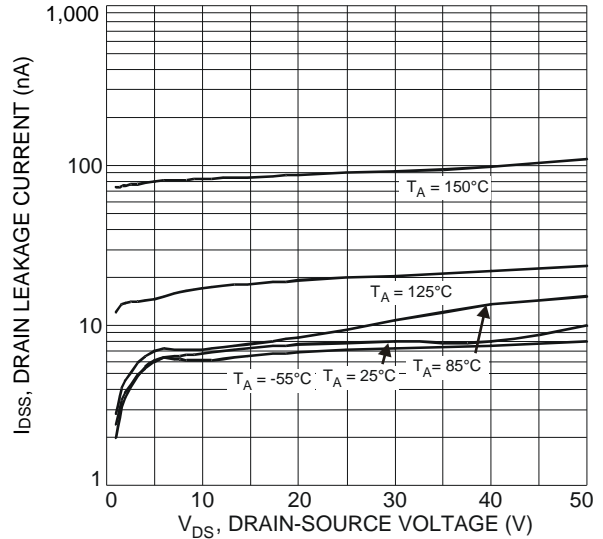


Figure 8. Typical Drain-Source Leakage Current vs. Voltage

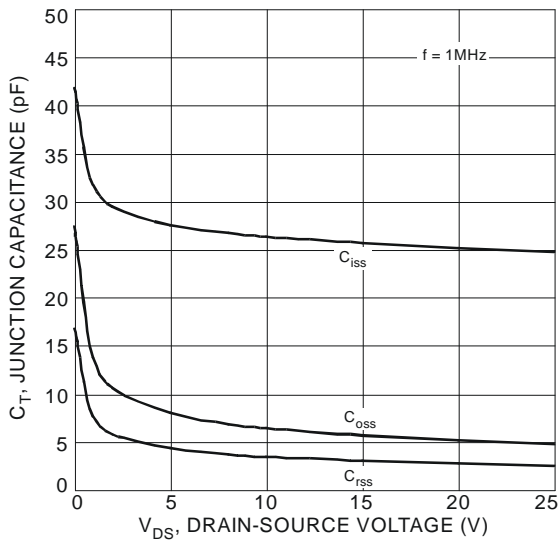
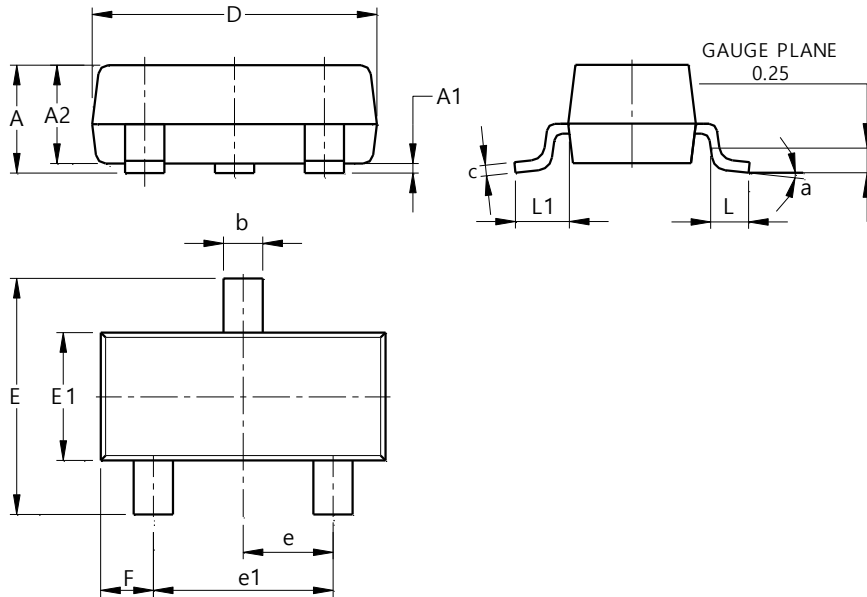


Figure 9. Typical Junction Capacitance

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)

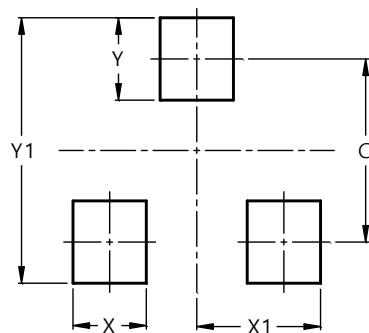


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

### SOT23 (Standard)



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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